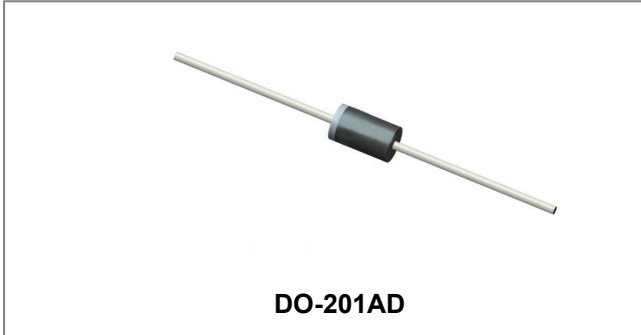


## SB20150 SCHOTTKY RECTIFIER



### Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Terminals finish: Tin Lead-free plated
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

### Maximum Ratings@T<sub>c</sub>=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-	150	V
Working Peak Reverse Voltage	V <sub>RWM</sub>			
DC Blocking Voltage	V <sub>R</sub>			
Average Rectified Forward Current	I <sub>F(AV)</sub>	T <sub>c</sub> =108°C, In DC	20	A
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	300	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 20A, Pulse, T <sub>J</sub> = 25 °C	0.85	1.05	V
	V <sub>F2</sub>	@ 20A, Pulse, T <sub>J</sub> = 125 °C	0.72	0.95	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = Rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 25 °C	0.0001	1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = Rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 125 °C	0.2	8	mA
Series Inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	2	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	1.02	g

**Ratings and Characteristics Curves**

Figure 1 Typical Forward Characteristics

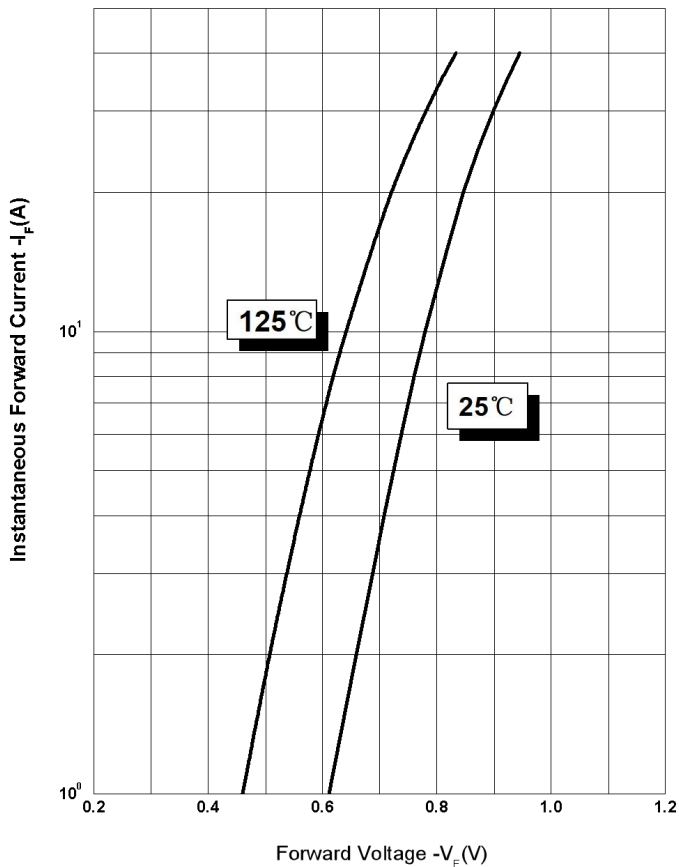


Figure 2 Typical Reverse Characteristics

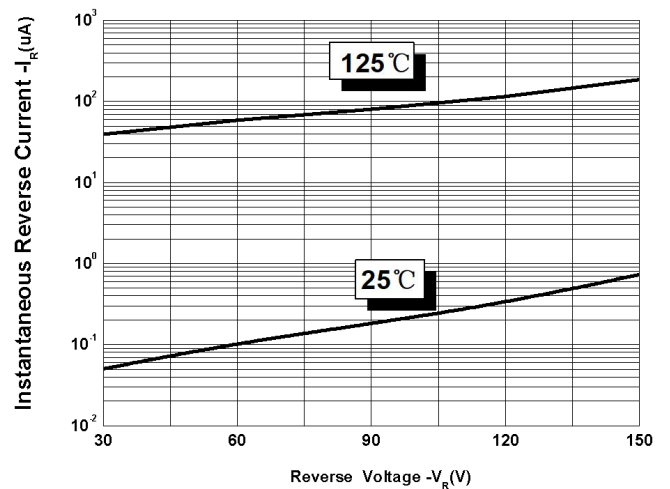
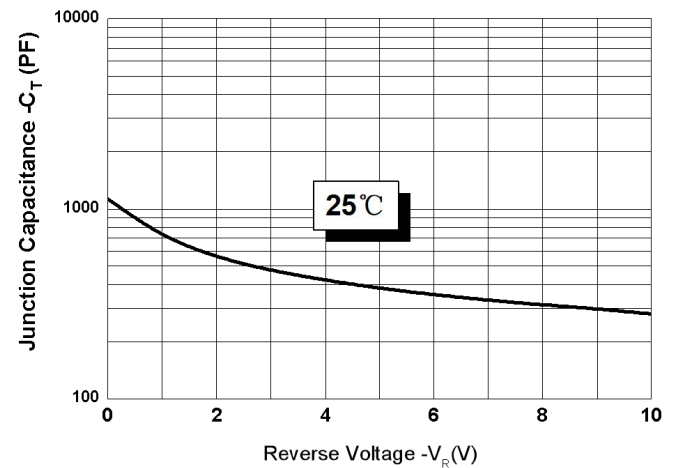
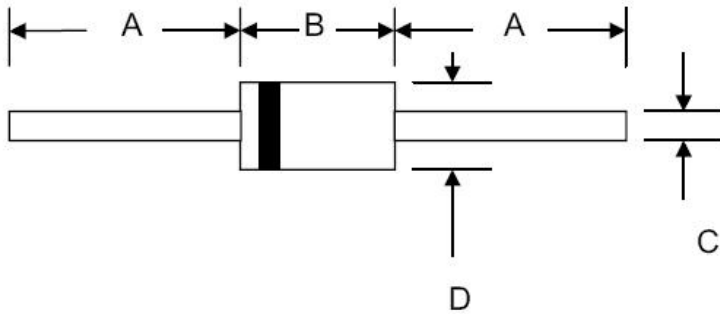


Figure 3 Typical Junction Capacitance



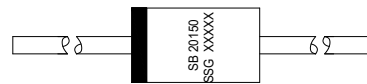
**Mechanical Dimensions DO-201AD**


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	25.4	-	1.000	-
B	8.50	9.50	0.335	0.374
C	1.2	1.3	0.048	0.052
D	5.0	5.6	0.197	0.220

**Ordering Information**

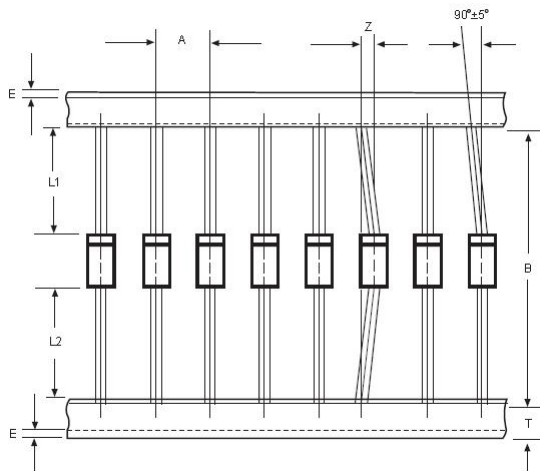
Device	Package	Shipping
SB20150	DO-201AD (Pb-Free)	1250pcs / tape
SB20150TA	DO-201AD (Pb-Free)	1250pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Marking Diagram**


Where XXXXX is YYWWL

SB20150 = Part Name  
 SSG = SSG  
 YY = Year  
 WW = Week  
 L = Lot Number

**Carrier Tape Specification DO-201AD**


SYMBOL	Millimeters	
	Min.	Max.
A	9.50	10.50
B	50.9	53.9
Z	-	1.20
T	5.60	6.40
E	-	0.80
IL1-L2I	-	1.0

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